Operational Amplifier, Railto-Rail, Low Voltage, Single and Dual

The LMV931 Single and LMV932 Dual are CMOS low-voltage operational amplifiers which can operate on single-sided power supplies (1.8 V to 5.0 V) with rail-to-rail input and output swing. Both devices come in small state-of-the-art packages and require very low quiescent current making them ideal for battery-operated, portable applications such as notebook computers and hand-held instruments. Rail-to-Rail operation provides improved signal-to-noise performance plus the small packages allow for closer placement to signal sources thereby reducing noise pickup.

The single LMV931 is offered in space saving SC70–5 package. The dual LMV932 is in either a Micro8 or SOIC package. These small packages are very beneficial for crowded PCB's.

Features

- Performance Specified on Single-Sided Power Supply: 1.8 V, 2.7 V, and 5 V
- Small Packages:

LMV931 in a SC-70 LMV932 in a Micro8 or SOIC-8

- No Output Crossover Distortion
- Extended Industrial Temperature Range: -40°C to +125°C
- Low Quiescent Current 210 μA, Max Per Channel
- No Output Phase-Reversal from Overdriven Input
- These are Pb-Free Devices

Typical Applications

- Notebook Computers, Portable Battery-Operated Instruments, PDA's
- Active Filters, Low-Side Current Monitoring

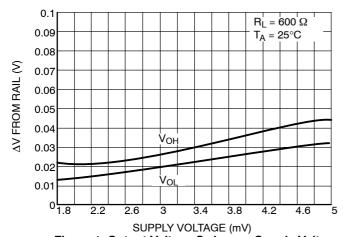


Figure 1. Output Voltage Swing vs. Supply Voltage



ON Semiconductor®

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MARKING DIAGRAMS

LMV931 (Single)



SC-70 CASE 419A





TSOP-5 CASE 483



M = Date Code

■ = Pb-Free Package

(*Note: Microdot may be in either location)

LMV932 (Dual)



Micro8[™] CASE 846A





SOIC-8 CASE 751



A = Assembly Location

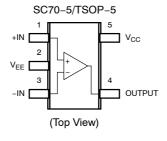
Y = Year
L = Wafer Lot
W = Work Week
Pb-Free Package

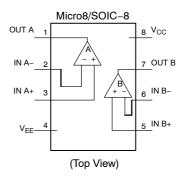
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 14 of this data sheet.

PIN CONNECTIONS





MAXIMUM RATINGS

Symbol	Rating	Value	Unit	
Vs	Supply Voltage (Operating Range V _S = 1.8 V to 5.5 V)	5.5	V	
V_{IDR}	Input Differential Voltage		± Supply Voltage	V
V _{ICR}	Input Common Mode Voltage Range	-0.5 to (V _{CC}) + 0.5	V	
	Maximum Input Current		10	mA
t _{So}	Output Short Circuit (Note 1)		Continuous	
T_J	Maximum Junction Temperature (Operating Range -40°C to	85°C)	150	°C
$\theta_{\sf JA}$	Thermal Resistance:	SC-70 TSOP-5 Micro8	280 333 238	°C/W
T _{stg}	Storage Temperature		-65 to 150	°C
	Mounting Temperature (Infrared or Convection ≤ 30 sec)		260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ESD data available upon request.

 Continuous short-circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V_{CC} or V_{EE} will adversely affect reliability.

1.8 V DC ELECTRICAL CHARACTERISTICS (Note 2) Unless otherwise noted, all min/max limits are guaranteed for $T_A = 25^{\circ}C$, $V_S = 1.8$ V, $V_{CM} = V_S/2$, $V_O = V_S/2$ and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	/oltage V _{IO} LMV931 (Single) (-40°C to +125°C)			1	6	mV
		LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	Ι _Β	−40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	-40°C to +125°C		< 1		nA
Supply Current	I _{CC}	In Active Mode		75	185	μΑ
(per Channel)		-40°C to +125°C			205	
Common Mode	CMRR	$0 \text{ V} \le \text{V}_{\text{CM}} \le 0.6 \text{ V}, 1.4 \text{ V} \le \text{V}_{\text{CM}} \le 1.8 \text{ V}$	50	70		dB
Rejection Ratio		– 40°C to +125°C	50			
		$-0.2 \text{ V} \leq \text{ V}_{\text{CM}} \leq 0 \text{ V}, 1.8 \text{ V} \leq \text{ V}_{\text{CM}} \leq 2 \text{ V}$	50	70		
Power Supply	PSRR	$1.8 \text{ V} \le \text{V}^+ \le 5 \text{ V}, \text{V}_{\text{CM}} = 0.5 \text{ V}$	50	70		dB
Rejection Ratio		-40°C to +125°C	50			
Input Common–Mode Voltage Range	Vсм	For CMRR ≥ 50 dB and T _A = 25°C	V _{EE} - 0.2	-0.2 to 2.1	V _{CC} + 0.2	V
		For CMRR ≥ 50 dB and T _A = - 40°C to +85°C	V _{EE}		V _{CC}	
		For CMRR \geq 50 dB and T _A = -40° C to $+125^{\circ}$ C	V _{EE} + 0.2		V _{CC} - 0.2	
Large Signal Voltage Gain LMV931 (Single)	A_V	R_L = 600 Ω to 0.9 V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	77	101		dB
		-40°C to +125°C	73			
		R_L = 2 k Ω to 0.9V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	80	105		
		-40°C to +125°C	75			
Large Signal Voltage	1	R_L = 600 Ω to 0.9 V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	75	90		
Gain LMV932 (Dual)		-40°C to +125°C	72			
		R_L = 2 k Ω to 0.9 V, V_O = 0.2 V to 1.6 V, V_{CM} = 0.5 V	78	100		
		-40°C to +125°C	75			
Output Swing	V _{OH}	R_L = 600 Ω to 0.9V, V_{IN} = \pm 100 mV	1.65	1.72		V
		-40°C to +125°C	1.63			
	V _{OL}	R_L = 600 Ω to 0.9V, V_{IN} = \pm 100 mV		0.077	0.105	
		-40°C to +125°C			0.12	
	V _{OH}	R_L = 2 k Ω to 0.9V, V_{IN} = \pm 100 mV	1.75	1.77		
		-40°C to +125°C	1.74			
	V _{OL}	R _L = 2 kΩ to 0.9 V, V _{IN} = \pm 100 mV		0.24	0.035	
		-40°C to +125°C			0.04	
Output Short Circuit	I _O	Sourcing, Vo = 0 V, V _{IN} = +100 mV	4.0	30		mA
Current		-40°C to +125°C	3.3			
		Sinking, Vo = 1.8V, V _{IN} = -100 mV	7.0	60		
		−40°C to +125°C	5.0			

^{2.} Guaranteed by design and/or characterization.

1.8 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for $T_A = 25$ °C, $V_S = 1.8$ V, $V_{CM} = V_S/2$, $V_0 = V_S/2$ and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	SR	(Note 3)		0.35		V/μS
Gain Bandwidth Product	GBWP			1.4		MHz
Phase Margin	Θm			67		٥
Gain Margin	Gm			7		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V _{CM} = 0.5 V		60		nV/√ Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = +1, R_L = 600 Ω , V_O = 1 V_{PP}		0.023		%
Amplifier-to-Amplifier Isolation		(Note 4)		123		dB

^{3.} Connected as voltage follower with input step from V_{EE} to V_{CC} . Number specified is the slower of the positive and negative slew rates. 4. Input referred, $R_L = 100 \text{ k}\Omega$ connected to $V_S/2$. Each amp excited in turn with 1 kHz to produce $V_O = 3 \text{ V}_{PP}$. (For Supply Voltages < 3 V,

2.7 V DC ELECTRICAL CHARACTERISTICS (Note 5) Unless otherwise noted, all min/max limits are guaranteed for T_A = 25°C, V_S = 2.7 V, V_{CM} = $V_S/2$, V_O = $V_S/2$ and R_L > 1 M Ω . Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Input Offset Voltage	V _{IO}	LMV931 (Single) (-40°C to +125°C)		1	6	mV
	-	LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	I _B	−40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	−40°C to +125°C		< 1		nA
Supply Current (per	I _{CC}	In Active Mode		80	190	μΑ
Channel)		-40°C to +125°C			210	
Common Mode	CMRR	$0~V \leq V_{CM} \leq 1.5~V, 2.3~V \leq V_{CM} \leq 2.7~V$	50	70		dB
Rejection Ratio	-	−40°C to +125°C	50			
	-	$-0.2 \text{ V} \leq \text{V}_{\text{CM}} \leq 0 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{CM}} \leq 2.9 \text{ V}$	50	70		
Power Supply	PSRR	$1.8~V \leq V^{+} \leq 5~V, V_{CM} = 0.5~V$	50	70		dB
Rejection Ratio	-	−40°C to +125°C	50			
Input Common-Mode Voltage Range	Vсм	For CMRR \geq 50 dB and T _A = 25°C	V _{EE} - 0.2	-0.2 to 3.0	V _{CC} + 0.2	V
		For CMRR \geq 50 dB and T _A = -40°C to +85°C	V _{EE}		V _{CC}	
		For CMRR \geq 50 dB and $T_A = -40^{\circ}C$ to $+125^{\circ}C$	V _{EE} + 0.2		V _{CC} - 0.2	
Large Signal Voltage	A_V	R_L = 600 Ω to 1.35 V, V_O = 0.2 V to 2.5 V	87	104		dB
Gain LMV931 (Single)	-	−40°C to +125°C	86			
		R_L = 2 k Ω to 1.35 V, V_O = 0.2 V to 2.5 V	92	110		
		−40°C to +125°C	91			
Large Signal Voltage	A_V	R_L = 600 Ω to 1.35 V, V_O = 0.2 V to 2.5 V	78	90		
Gain LMV932 (Dual)		−40°C to +125°C	75			
		$R_L = 2~k\Omega$ to 1.35 V, V_O = 0.2 V to 2.5 V	81	100		
		−40°C to +125°C	78			
Output Swing	V _{OH}	R_L = 600 Ω to 1.35 V, V_{IN} = ±100 mV	2.55	2.62		V
		−40°C to +125°C	2.53			
	V _{OL}	R_L = 600 Ω to 1.35 V, V_{IN} = ±100 mV		0.083	0.11	
		-40°C to +125°C			0.13	
	V _{OH}	R_L = 2 k Ω to 1.35 V, V_{IN} = $\pm100~mV$	2.65	2.675		
		-40°C to +125°C	2.64			
	V _{OL}	R_L = 2 k Ω to 1.35 V, V_{IN} = ±100 mV		0.025	0.04	
		-40°C to +125°C			0.045	
Output Short Circuit	I _O	Sourcing, Vo = 0 V, $V_{IN} = \pm 100 \text{ mV}$	20	65		mA
Current		-40°C to +125°C	15			
		Sinking, Vo = 0 V, $V_{IN} = -100 \text{ mV}$	18	75		
		-40°C to +125°C	12			

^{5.} Guaranteed by design and/or characterization.

2.7 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for $T_A = 25$ °C, $V_S = 2.7$ V, $V_{CM} = V_S/2$, $V_O = V_S/2$ and $R_L > 1$ M Ω . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	SR	(Note 6)		0.4		V/uS
Gain Bandwidth Product	GBWP			1.4		MHz
Phase Margin	Θm			70		0
Gain Margin	Gm			7.5		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V _{CM} = 1.0 V		57		nV/√ Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = +1, R_L = 600 Ω , V_O = 1 V_{PP}		0.022		%
Amplifier-to-Amplifier Isolation		(Note 7)		123		dB

^{6.} Connected as voltage follower with input step from V_{EE} to V_{CC} . Number specified is the slower of the positive and negative slew rates.

7. Input referred, $R_L = 100 \text{ k}\Omega$ connected to $V_S/2$. Each amp excited in turn with 1 kHz to produce $V_O = 3 \text{ V}_{PP}$. (For Supply Voltages < 3 V,

5 V DC ELECTRICAL CHARACTERISTICS (Note 8) Unless otherwise noted, all min/max limits are guaranteed for T_A = 25°C, V_S = 5 V, V_{CM} = V_S /2, V_O = V_S /2 and R_L > 1 M Ω . Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Input Offset Voltage	et Voltage V _{IO} LMV931 (Single) (-40°C to +125°C)			1	6	mV
		LMV932 (Dual) (-40°C to +125°C)		1	7.5	
Input Offset Voltage Average Drift	TCV _{IO}			5.5		μV/°C
Input Bias Current	Ι _Β	-40°C to +125°C		< 1		nA
Input Offset Current	I _{IO}	−40°C to +125°C		< 1		nA
Supply Current (per	I _{CC}	In Active Mode		95	210	μΑ
Channel)		−40°C to +125°C			230	
Common-Mode	CMRR	0 V \leq V _{CM} \leq 3.8 V, 4.6 V \leq V _{CM} \leq 5.0 V	50	70		dB
Rejection Ratio		−40°C to +125°C	50			
		$-0.2 \text{ V} \leq \text{V}_{\text{CM}} \leq 0 \text{ V}, 5.0 \text{ V} \leq \text{V}_{\text{CM}} \leq 5.2 \text{V}$	50	70		
Power Supply	PSRR	$1.8 \text{ V} \leq \text{V}^+ \leq 5 \text{ V}, \text{V}_{\text{CM}} = 0.5 \text{ V}$	50	70		dB
Rejection Ratio		−40°C to +125°C	50			
Input Common–Mode Voltage Range	Vсм	For CMRR ≥ 50 dB and $T_A = 25^{\circ}C$	V _{EE} - 0.2	-0.2 to 5.3	V _{CC} + 0.2	V
		For CMRR \geq 50 dB and T _A = -40° C to $+85^{\circ}$ C	V _{EE}		V _{CC}]
		For CMRR \geq 50 dB and T _A = -40° C to $+125^{\circ}$ C	V _{EE} + 0.3		V _{CC} - 0.3	
Large Signal Voltage Gain LMV931 (Single)	A _V	R_L = 600 Ω to 2.5 V, V_O = 0.2 V to 4.8 V	88	102		dB
	-	−40°C to +125°C	87			
		R_L = 2 k Ω to 2.5 V, V_O = 0.2 V to 4.8 V	94	113		
		−40°C to +125°C	93			
Large Signal Voltage	A _V	R_L = 600 Ω to 2.5 V, V_O = 0.2 V to 4.8 V	81	90		
Gain LMV932 (Dual)		−40°C to +125°C	78			
		R_L = 2 k Ω to 2.5 V, V_O = 0.2 V to 4.8 V	85	100		
		−40°C to +125°C	82			
Output Swing	V _{OH}	R_L = 600 Ω to 2.5 V, V_{IN} = \pm 100 mV	4.855	4.89		V
		−40°C to +125°C	4.835			
	V _{OL}	R_L = 600 Ω to 2.5 V, V_{IN} = ±100 mV		0.12	0.16	
		−40°C to +125°C			0.18	
	V _{OH}	R_L = 2 k Ω to 2.5 V, V_{IN} = ± 100 mV	4.945	4.967		
		−40°C to +125°C	4.935			
	V _{OL}	R_L = 2 k Ω to 2.5 V, V_{IN} = ±100 mV		0.037	0.065	
		-40°C to +125°C			0.075	
Output Short-Circuit	I _O	Sourcing, Vo = 0 V, V_{IN} = +100 mV	55	65		mA
Current		-40°C to +125°C	45			
		Sinking, Vo = 5 V, V _{IN} = -100 mV	58	80		
		-40°C to +125°C	45			

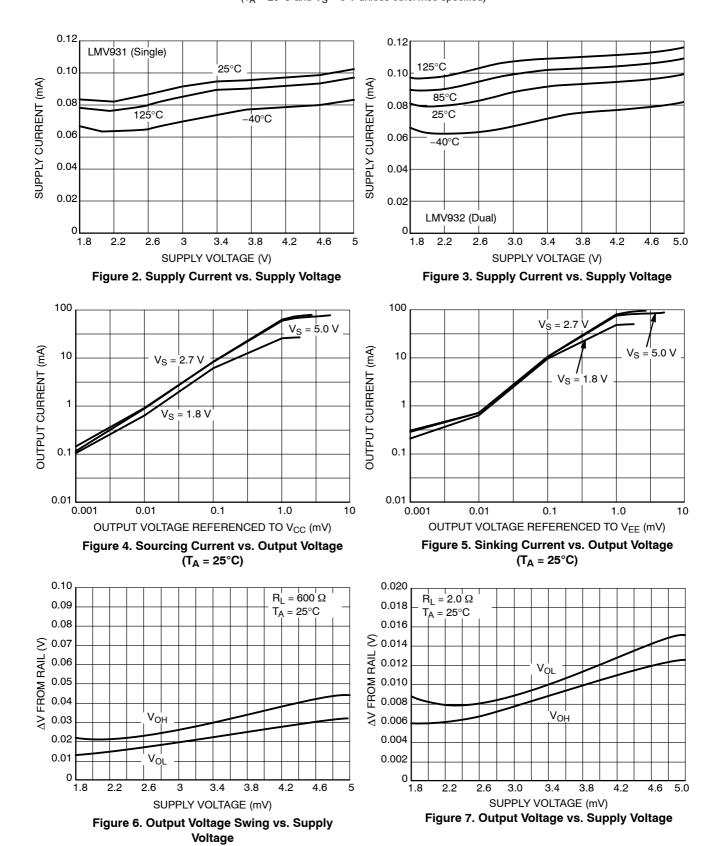
^{8.} Guaranteed by design and/or characterization.

5 V AC ELECTRICAL CHARACTERISTICS Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_S = 5 V, V_{CM} = $V_S/2$, V_O = $V_S/2$ and R_L > 1 $M\Omega$. Typical specifications represent the most likely parametric norm.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	SR	(Note 9)		0.48		V/uS
Gain Bandwidth Product	GBWP			1.5		MHz
Phase Margin	Θm			65		0
Gain Margin	Gm			8		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz, V _{CM} = 2 V		50		nV/√ Hz
Total Harmonic Distortion	THD	f = 1 kHz, A_V = +1, R_L = 600 Ω , V_O = 1 V_{PP}		0.022		%
Amplifier-to- Amplifier Isolation		(Note 10)		123		dB

^{9.} Connected as voltage follower with input step from V_{EE} to V_{CC} . Number specified is the slower of the positive and negative slew rates. 10. Input referred, R_L = 100 k Ω connected to $V_S/2$. Each amp excited in turn with 1 kHz to produce V_O = 3 V_{PP} . (For Supply Voltages < 3 V, V_O = V_{CC}).

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

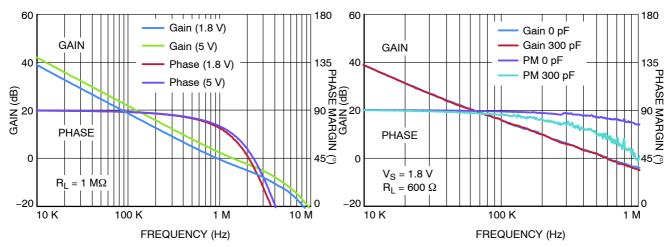


Figure 8. Open Loop Gain and Phase

Figure 9. Frequency Response vs. CL

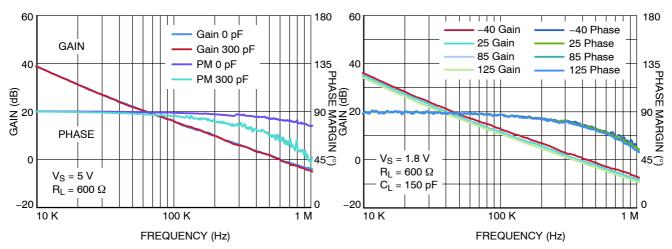


Figure 10. Frequency Response vs. CL

Figure 11. Gain and Phase vs. Temp

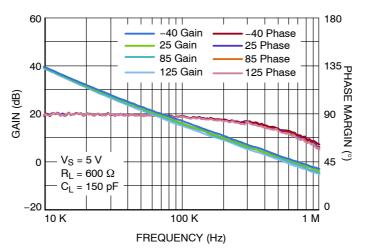


Figure 12. Gain and Phase vs. Temp

TYPICAL CHARACTERISTICS

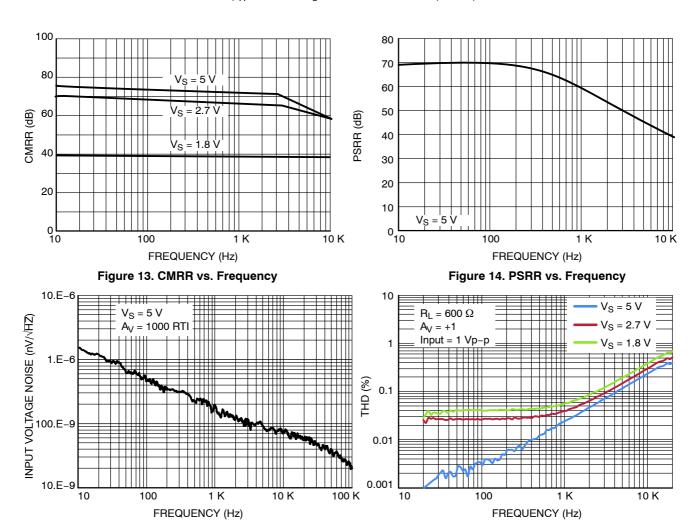


Figure 15. Input Voltage Noise vs. Frequency

Figure 16. THD vs. Frequency

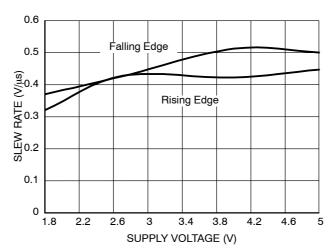


Figure 17. Slew Rate vs. Supply Voltage

TYPICAL CHARACTERISTICS

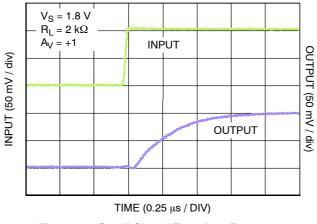


Figure 18. Small Signal Transient Response

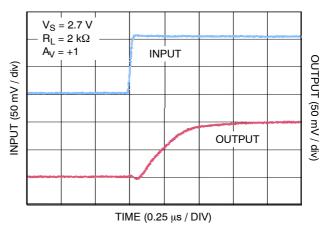


Figure 19. Small Signal Transient Response

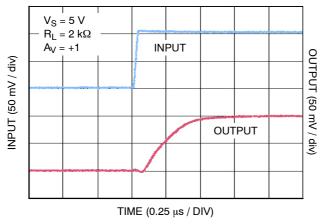


Figure 20. Small Signal Transient Response

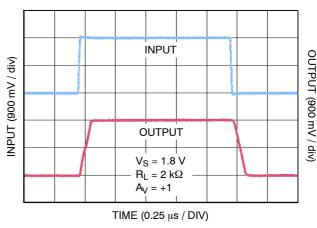


Figure 21. Large Signal Transient Response

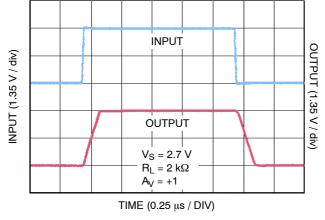


Figure 22. Large Signal Transient Response

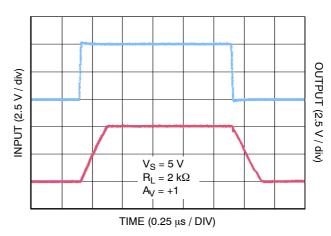
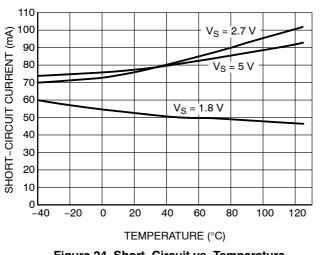


Figure 23. Large Signal Transient Response

TYPICAL CHARACTERISTICS

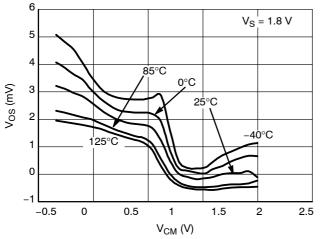
 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



110 100 SHORT-CIRCUIT CURRENT (mA) 90 V_S = 5 V 80 70 $V_{S} = 2.7 V$ 60 50 40 30 20 V_S = 1.8 V 10 -20 -40 60 80 100 120 TEMPERATURE (°C)

Figure 24. Short-Circuit vs. Temperature (Sinking)

Figure 25. Short-Circuit vs. Temperature (Sourcing)



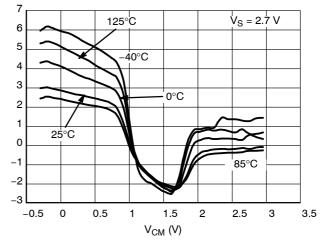
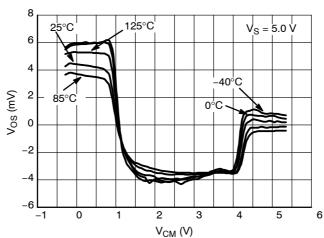


Figure 26. Offset Voltage vs. Common Mode Range V_{DD}

Figure 27. Offset Voltage vs. Common Mode Range



Vos (mV)

Figure 28. Offset Voltage vs. Common Mode Range

APPLICATION INFORMATION

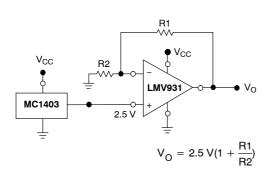


Figure 29. Voltage Reference

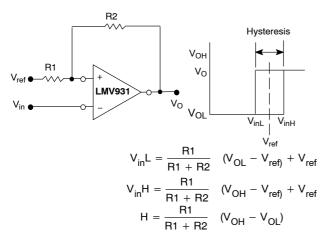


Figure 31. Comparator with Hysteresis

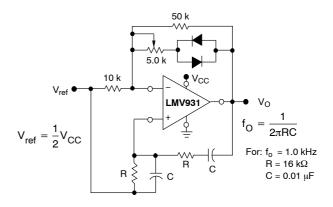
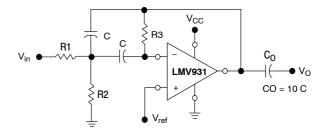


Figure 30. Wien Bridge Oscillator



Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value f_o , C Q Then : $R3 = \frac{Q}{\pi f_O C}$ $R1 = \frac{R3}{2 \, A(f_O)}$ $R2 = \frac{R1 \, R3}{4Q^2 \, R1 \, - R3}$

For less than 10% error from operational amplifier, (($Q_O f_O$)/BW) < 0.1 where f_O and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 32. Multiple Feedback Bandpass Filter

ORDERING INFORMATION

Order Number	Number of Channels	Number of Pins	Package Type	Shipping [†]
LMV931SQ3T2G	Single	5	SC70-5 (Pb-Free)	3000 / Tape & Reel
LMV931SN3T1G	Single	5	TSOP-5 (Pb-Free)	3000 / Tape & Reel
LMV932DMR2G*	Dual	8	Micro8 (Pb-Free)	4000 / Tape & Reel
LMV932DR2G	Dual	8	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Micro8 is a trademark of International Rectifier.

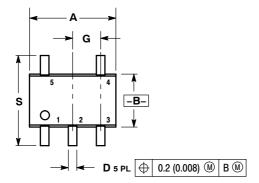
^{*}Consult Sales.

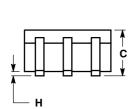


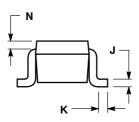
SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L

DATE 17 JAN 2013

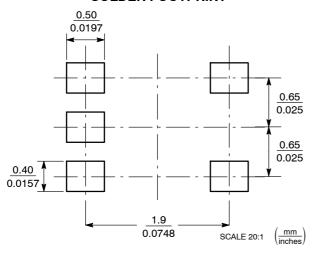
SCALE 2:1







SOLDER FOOTPRINT



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- 419A-01 OBSOLETE. NEW STANDARD 419A-02.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008	REF	0.20	REF	
S	0.079	0.087	2.00	2.20	

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This infomration is generic. Please refer to device data sheet for actual part marking.

STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3

5. CATHODE 4

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE 1	PIN 1. SOURCE 1
2. EMITTER	2. EMITTER	2. N/C	2. DRAIN 1/2
3. BASE	3. BASE	3. ANODE 2	3. SOURCE 1
4. COLLECTOR	4. COLLECTOR	4. CATHODE 2	4. GATE 1
5. COLLECTOR	5. CATHODE	5. CATHODE 1	5. GATE 2
STYLE 6:	STYLE 7:	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9:
PIN 1. EMITTER 2	PIN 1. BASE		PIN 1. ANODE
2. BASE 2	2. EMITTER		2. CATHODE
3. EMITTER 1	3. BASE		3. ANODE
4. COLLECTOR	4. COLLECTOR		4. ANODE
5. COLLECTOR 2/BASE 1	5. COLLECTOR		5. ANODE

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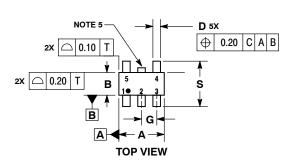
ISSUE	REVISION	DATE
С	CONVERTED FROM PAPER DOCUMENT TO ELECTRONIC. REQ. BY N LAFEB-RE.	20 JUN 1998
D	CONVERTED FROM MOTOROLA TO ON SEMICONDUCTOR. ADDED STYLE 5. REQ. BY E. KIM.	24 JUL 2000
Е	ADDED STYLES 6 & 7. REQ. BY S. BACHMAN.	03 AUG 2000
F	DELETED DIMENSION V, WAS 0.3-0.44MM/0.012-0.016IN. REQ. BY G. KWONG.	14 JUN 2001
G	ADDED STYLE 8, REQ. BY S. CHANG; ADDED STYLE 9, REQ. BY S. BACHMAN; ADDED NOTE 4, REQ. BY S. RIGGS	25 JUN 2003
Н	CHANGED STYLE 6. REQ. BY C. LIM	28 APR 2005
J	CHANGED TITLE DESCRIPTION. REQ. BY B. LOFTS.	31 AUG 2005
K	CORRECTED TITLE AND DESCRIPTION TO SC-88A (SC-70-5/SOT-353). CORRECTED MARKING DIAGRAM. REQ. BY D. TRUHITTE.	13 JUL 2010
L	ADDED SOLDER FOOTPRINT. REQ. BY I. MARIANO.	17 JAN 2013
	<u> </u>	

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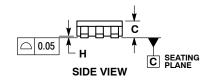


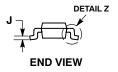
TSOP-5 **CASE 483 ISSUE N**

DATE 12 AUG 2020







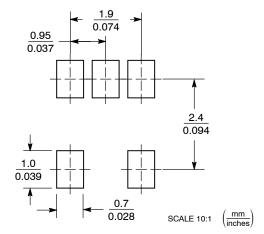


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE
 MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.85	3.15	
В	1.35	1.65	
C	0.90	1.10	
D	0.25	0.50	
G	0.95 BSC		
Н	0.01 0.10		
J	0.10	0.26	
K	0.20	0.60	
М	0° 10°		
S	2.50	3.00	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location

= Date Code = Year = Pb-Free Package

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

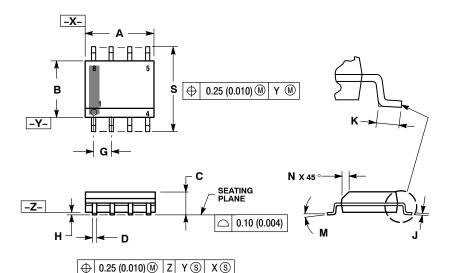
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SOIC-8 NB CASE 751-07 **ISSUE AK**

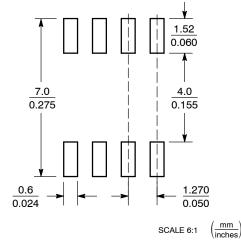
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		MILLIMETERS INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10 0.25		0.004 0.01	
7	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 ° 8 °		0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

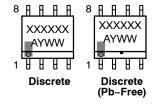
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww

= Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 3: PIN 1. DRAIN, PIE #1 CTOR, #1 CTOR, #2 CTOR, #1 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #1	2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #1 Vd STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #1 4. ANODE 5. ANODE 6. ANODE 7. ANODE 7. ANODE 7. ANODE 7. ANODE 8. COMMON CATHODE 8. COMMON CATHODE 9. ANODE 7. ANODE 8. COMMON CATHODE 9. ANODE 9. ANO
E PIN 1. INPUT 2. EXTERNAL BY 3. THIRD STAGE 4. GROUND E 5. DRAIN 6. GATE 3 7. SECOND STAGE 8. FIRST STAGE STYLE 11: ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 ID	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 Vd 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 STYLE 15: RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
STYLE 15: RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
N 7. CATHODE, CON N 8. CATHODE, CON	MMON 5. COLLECTOR, DIE #2 MMON 6. COLLECTOR, DIE #2 MMON 7. COLLECTOR, DIE #1 MMON 8. COLLECTOR, DIE #1
STYLE 19: PIN 1. SOURCE 1 E 2. GATE 1 E 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 DE 7. DRAIN 1 DE 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 23: E1 PIN 1. LINE 1 IN DN CATHODE/VCC 2. COMMON ANC DN CATHODE/VCC 3. COMMON ANC E3 4. LINE 2 IN DN ANODE/GND 5. LINE 2 OUT E4 6. COMMON ANC E5 7. COMMON ANC DN ANODE/GND 8. LINE 1 OUT	ODE/GND 2. EMITTER ODE/GND 3. COLLECTOR/ANODE
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V MON 6. VBULK 7. VBULK 8. VIN
1 1	
;	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ E 5. SOURCE E 6. SOURCE E 7. SOURCE 8. DRAIN

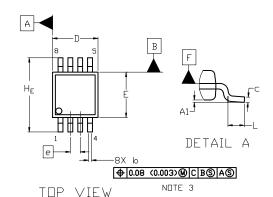
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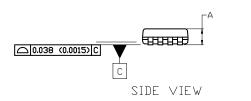
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Micro8 CASE 846A-02 ISSUE K

DATE 16 JUL 2020

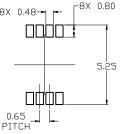






NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DDES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



RECOMMENDED MOUNTING FOOTPRINT

MID	MI	LLIMETE	RS
DIM	MIN.	N□M.	MAX.
Α	-	-	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
С	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
HE	4.75	4.90	5.05
L	0.40	0.55	0.70

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
SOURCE	2. GATE 1	2. N-GATE
SOURCE	3. SOURCE 2	P-SOURCE
GATE	4. GATE 2	4. P-GATE
DRAIN	5. DRAIN 2	5. P-DRAIN
DRAIN	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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